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Preface

The 41st IRPS proceedings is the culmination of 1000's of hours of author, committee and volunteer labor. It represents state-of-the-art in microelectronic reliability. In addition to a record number of submitted technical works, industry leaders from TSMC, Intel and Texas Instruments addressed the attendees. In keeping with the ever changing semiconductor industry, two keynote addresses were organized: one by Dr. Shang-yi Chiang, senior vice president and head of research and development group, of Taiwan Semiconductor Manufacturing Co., Ltd. (TSMC), "Technology and reliability challenges in the foundry business". And, one by Mark T. Bohr, an Intel Senior Fellow and director of process architecture and integration at Intel, "Technology and reliability challenges at integrated device manufacturers." At the Symposium Reception and Poster Session the speaker was Larry Hornbeck, Texas Instruments Fellow, Digital Light Processing, "The future of MEMS based projection display systems." Finally, a new "Reliability Year-in-Review" Seminar was added to the end of the IRPS.

The companion CDROM of the proceedings (IEEE Catalog No. 03CH37400C; ISBN: 0-7803-7650-1) contain many files where color is used and in some cases make viewing data graphs easier. Abstracts of the Sunday and Monday tutorials can be found in the last two pages of these proceedings.

A virtual IRPS 2003 on DVD-ROMs is available (www.irps.org) that provides video, audio, and presentation material for all the presentations.

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